

2825

Attorney Docket No.: <u>NICHIA-00800</u>

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Shinichi Nagahama et al.

Serial No.: 09/500,288 \

Filed: February 8, 2000

For: **NITRIDE SEMICONDUCTOR**

DEVICE AND MANUFACTURING)

METHOD THEREOF

Group:

Art Unit: 2825

Examiner:

TRANSMITTAL LETTER

260 Sheridan Avenue, Suite 420

Palo Alto, CA 94306

(650) 833-0160

Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

Enclosed please find an Information Disclosure Statement and Form PTO-1449, including copies of the references contained thereon, for filing in the U.S. Patent and Trademark Office.

The Commissioner is hereby authorized to charge any additional fee or credit overpayment to our Deposit Account No. <u>08-1275</u>. An originally executed duplicate of this transmittal is enclosed for this purpose.

Respectfully submitted,

HAVERSTOCK & OWENS LLP

Dated: 9 - 8 - 6

Thomas B. Haverstock

Reg. No.: 32,571

Attorneys for Applicants

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:) Group Art Unit: 2825
Shinichi Nagahama <i>et al</i> .) Examiner:
Serial No.: 09/500,288)) <u>INFORMATION DISCLOSURE</u>) STATEMENT
Filed: February 8, 2000) 260 Sheridan Avenue, Suite 420
For: NITRIDE SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF	Palo Alto, California 94306

Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

The citations listed below, copies attached, may be material to the examination of the above-identified application, and are therefore submitted in compliance with the duty of disclosure defined in 37 C.F.R. §§ 1.56 and 1.97. The Examiner is requested to make these citations of official record in this application.

Applicants have become aware of the following printed publications which may be material to the examination of this application:

- Japanese Publication No.: 04144294;
- Japanese Publication No.: 09180998;
- Japanese Publication No.: 09246651;
- Japanese Publication No.: 09260772;
- Japanese Publication No.: 09293935;
- Japanese Publication No.: 10242565;
- Japanese Publication No.: 10256645;
- Japanese Publication No.: 10270792;

<u>PATENT</u>

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• Japanese Publication No.: 10290027;

• Japanese Publication No.: 10294529:

Japanese Publication No.: 10321962;

Japanese Publication No.: 11040893;

Japanese Publication No.: 2000-31599;

German Publication No.: DE 196 48 955A1; and

 "InGaN/GaN/AIGaN-based laser diodes with modulation-doped strained-layer superlattices grown on an epitaxially laterally overgrown GaN substrate," Shuji Nakamura et al., Applied Physics Letter, Vol. 72, No. 2, January 12, 1998...

This Information Disclosure Statement under 37 C.F.R. §§ 1.56 and 1.97 is not to be construed as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that anyone or more of these citations constitutes prior art.

Respectfully submitted,

HAVERSTOCK & OWENS LLP

Dated: 9-8-00

Thomas B. Haverstock Reg. No.: 32,571

Attorneys for Applicants

CERTIFICATE OF MAILING (37 CFR \$ 1.8(a))

Chereby certify that this paper valong with any referred to a lend attached to enclosed) sible and deposited with the Colonia Security on the date shown be on the sufficient postage as first class multiple on a sign roughly and the Assistant pages size to the Assistant pages size to the training amounts size to make it was notice up 2,0231.

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